Rochester Electronics

Datasheet

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceed the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
    - Class Q Military
    - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)

- Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

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CA3127

Complete data sheet available via web. Harris' home page: http://www.semi.harris.com/ or via Harris Anston BBS. See Section 10

August 1996

High Frequency NPN Transistor Array

Features

- Gain Bandwidth Product (f_T) . . . . . >1GHz
- Power Gain . . . . . 30dB (Typ) at 100MHz
- Noise Figure . . . . . 3.5dB (Typ) at 100MHz
- Five Independent Transistors on a Common Substrate

Applications

- VHF Amplifiers
- Multifunction Combinations - RF/Mixer/Oscillator
- Sense Amplifiers
- Synchronous Detectors
- VHF Mixers
- IF Converter
- IF Amplifiers
- Synthesizers
- Cascade Amplifiers

Description

The CA3127 consists of five general purpose silicon NPN transistors on a common monolithic substrate. Each of the completely isolated transistors exhibits low 1/f noise and a value of f_T in excess of 1GHz, making the CA3127 useful from DC to 500MHz. Access is provided to each of the terminals for the individual transistors and a separate substrate connection has been provided for maximum application flexibility. The monolithic construction of the CA3127 provides close electrical and thermal matching of the five transistors.

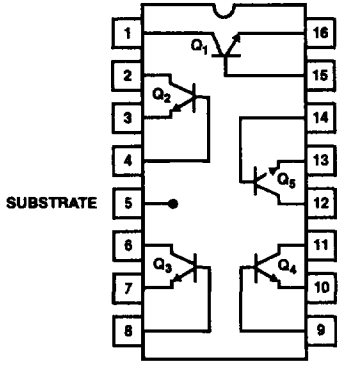
Ordering Information

PART NUMBER (BRAND)	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CA3127E	-55 to 125	16 Ld PDIP	E16.3
CA3127M (3127)	-55 to 125	16 Ld SOIC	M16.15
CA3127M96 (3127)	-55 to 125	16 Ld SOIC Tape and Reel	M16.15

5 STANDARD PRODUCTS

Pinout

CA3127
(PDIP, SOIC)
TOP VIEW



CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper IC Handling Procedures.

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